

RF3163 3V 900 MHZ LINEAR POWER AMPLIFIER MODULE

RoHS Compliant & Pb-Free Product Package Style: QFN, 16-Pin, 3 x 3

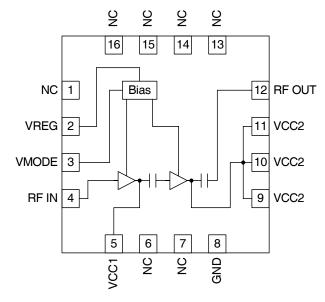


Features

- Input Internally Matched@50Ω
- Output Internally Matched
- 28dBm Linear Output Power
- 41% Peak Linear Efficiency -CDMA
- -51dBc ACPR @ 885kHz
- 55% AMPS Efficiency

Applications

- 3V CDMA/AMPS Cellular Handset
- 3V CDMA2000/1XRTT Cellular Handset
- 3V W-CDMA US-Cellular Handset
- 3V CDMA2000/1X-EV-D0 US-Cellular Handset
- Spread-Spectrum System



Functional Block Diagram

Product Description

The RF3163 is a high-power, high-efficiency linear amplifier module specifically designed for 3V handheld systems. The device is manufactured on an advanced third generation GaAs HBT process, and was designed for use as the final RF amplifier in 3V IS-95/CDMA2000-1X/AMPS/W-CDMA handheld digital cellular equipment, spread-spectrum systems, and other applications in the 824MHz to 849MHz band. The RF3163 has a digital control line for low power applications to lower quiescent current. The RF3163 is assembled in a 16-pin, 3mmx3mm, QFN package.

Ordering Information

RF31633V 900MHz Linear Power Amplifier ModuleRF3163PCBA-41XFully Assembled Evaluation Board

Optimum Technology Matching® Applied

🗹 GaAs HBT	□ SiGe BiCMOS	🗌 GaAs pHEMT	🗌 GaN HEMT
GaAs MESFET	Si BiCMOS	🗌 Si CMOS	
🗌 InGaP HBT	SiGe HBT	🗌 Si BJT	

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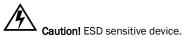
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RF3163



Absolute Maximum Ratings

Parameter	Rating	Unit		
Supply Voltage (RF off)	+8.0	V		
Supply Voltage ($P_{OUT} \leq 31 dBm$)	+5.2	V		
Control Voltage (V _{REG})	+3.9	V		
Input RF Power	+10	dBm		
Mode Voltage (V _{MODE})	+3.9	V		
Operating Temperature	-30 to +110	°C		
Storage Temperature	-40 to +150	°C		
Moisture Sensitivity Level (IPC/JEDEC J-STD-20)	MSL 2 @ 260 °C			



Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

RoHS status based on EU Directive 2002/95/EC (at time of this document revision).

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Parameter	Specification		Unit	Condition		
Farameter	Min.	Тур.	Max.	Unit	Condition	
High Power Mode - CDMA (V _{MODE} Low)					T=25°C Ambient, V_{CC} =3.4V, V_{REG} =2.8V, V_{MODE} =0V, and P_{OUT} =28dBm for all parameters (unless otherwise specified).	
Operating Frequency Range	824		849	MHz		
Linear Gain	26.0	28.5		dB		
Second Harmonics		-35	-30	dBc		
Third Harmonics		-40	-30	dBc		
Maximum Linear Output	28					
Linear Efficiency	37	41		%		
Maximum I _{CC}		455	501	mA		
ACPR @ 885 kHz		-51	-46	dBc		
ACPR @ 1.98 MHz		-58	-55	dBc		
Input VSWR		2:1				
Stability in Band			6:1		No oscillation>-70dBc	
Stability out of Band			10:1		No damage	
Noise Power		-133		dBm/Hz	At 45MHz offset.	
Low Power Mode - CDMA (V _{MODE} High)					$\label{eq:transform} \begin{array}{l} T{=}25^{\circ}C \text{ Ambient, } V_{CC}{=}3.4V, V_{REG}{=}2.8V, \\ V_{MODE}{=}2.8V, \text{and } P_{OUT}{=}18dBm \text{ for all parameters (unless otherwise specified).} \end{array}$	
Operating Frequency Range	824		849	MHz		
Linear Gain	21	24		dB		
Maximum Linear Output	18					
Maximum I _{CC}		125	156	mA	P _{OUT} =16dBm	
ACPR @885 kHz		-51	-46	dBc		
ACPR @1.98MHz		-61	-56	dBc		
Input VSWR		2:1				
Output VSWR Stability			6:1		No oscillation>-70dBc	
			10:1		No damage	

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RF3163

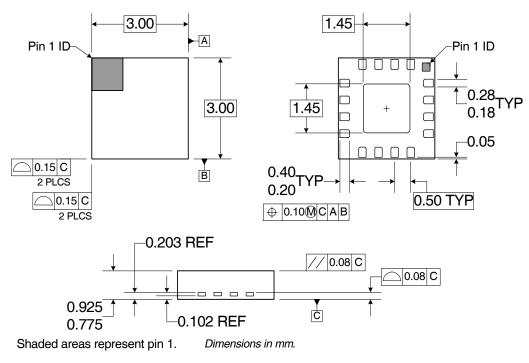
Devenetar	Specification			Unit	Condition	
Parameter	Min.	Тур.	Max.	Unit	Condition	
High Power Mode - W-CDMA (V _{MODE} Low)					T=25 ^o C Ambient, V_{CC} =3.4V, V_{REG} =2.8V, V_{MODE} =0V, and P_{OUT} =28dBm for all parameters (unless otherwise specified).	
Operating Frequency Range	824		849	MHz		
Linear Gain		28.5		dB		
Maximum Linear Output	28					
Linear Efficiency		45		%		
Maximum I _{CC}		410		mA		
ACLR @ 5 MHz		-41		dBc		
ACLR @ 10 MHz		-55		dBc		
Low Power Mode - W-CDMA (V _{MODE} High)					$\label{eq:VCC} \begin{array}{l} T{=}25^{o}C \mbox{ Ambient, } V_{CC}{=}3.4 \mbox{ V}, V_{REG}{=}2.8 \mbox{ V}, \\ V_{MODE}{=}2.8 \mbox{ V, and } P_{OUT}{=}18 \mbox{ dBm for all parameters (unless otherwise specified).} \end{array}$	
Operating Frequency Range	824		849	MHz		
Linear Gain		24		dB		
Maximum Linear Output	18					
Maximum I _{CC}		120		mA	P _{OUT} =16dBm	
ACLR @ 5 MHz		-41		dBc		
ACLR @ 10 MHz		-60		dBc		
FM Mode					T=25 ^o C Ambient, V_{CC} =3.4V, V_{REG} =2.8V, V_{MODE} =0V, and P_{OUT} =31dBm for all parameters (unless otherwise specified).	
Operating Frequency Range	824		849	MHz		
AMPS Maximum Output Power		31		dBm		
AMPS Efficiency	48	55		%		
AMPS Gain	25.5	28				
AMPS Second Harmonics		-35	-30	dBc		
AMPS Third Harmonics		-40	-30	dBc		
Power Supply						
Supply Voltage	3.2	3.4	4.2	V		
High Gain Idle Current		55	80	mA	V_{MODE} =low and V_{REG} =2.8V	
Low Gain Idle Current		45	70	mA	V_{MODE} =high and V_{REG} =2.8V	
V _{REG} Current		4.5	5.5	mA	V _{MODE} =high	
V _{MODE} Current		250	1000	uA		
RF Turn On/Off Time			6	uS		
DC Turn On/Off Time			40	uS		
Total Current (Power Down)		0.2	2.0	uA		
V _{REG} Low Voltage	0		0.5	V		
V _{REG} High Voltage (Recommended)	2.75	2.8	2.95	V		
V _{REG} High Voltage (Operational)	2.7		3.0	V		
V _{MODE} Voltage	0		0.5	V	High Gain Mode	
	2.0		3.0	V	Low Gain Mode	

RF3163

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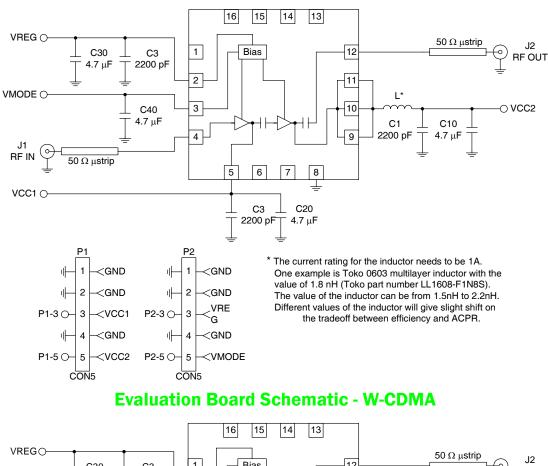
Pin	Function	Description	Interface Schematic
1	NC	No connection. Do not connect this pin to any external circuit.	
2	VREG	Regulated voltage supply for amplifier bias circuit. In power down mode, both V_{REG} and V_{MODE} need to be LOW (<0.5V).	
3	VMODE	For nominal operation (High Power mode), V _{MODE} is set LOW. When set HIGH, devices are biased lower to improve efficiency.	
4	RF IN	RF input internally matched to $50\Omega.$ This input is internally AC-coupled.	
5	VCC1	First stage collector supply. A 2200 pF and 4.7 μF decoupling capacitor are required.	
6	NC	No connection. Do not connect this pin to any external circuit.	
7	NC	No connection. Do not connect this pin to any external circuit.	
8	GND	Ground connection.	
9	VCC2	Output stage collector supply. Please see the schematic for required exter- nal components.	
10	VCC2	Same as pin 9.	
11	VCC2	Same as pin 9.	
12	RF OUT	RF output. Internally AC-coupled.	
13	NC	No connection. Do not connect this pin to any external circuit.	
14	NC	No connection. Do not connect this pin to any external circuit.	
15	NC	No connection. Do not connect this pin to any external circuit.	
16	NC	No connection. Do not connect this pin to any external circuit.	
Pkg Base	GND	Ground connection. The backside of the package should be soldered to a top side ground pad which is connected to the ground plane with multiple vias. The pad should have a short thermal path to the ground plane.	

Package Drawing

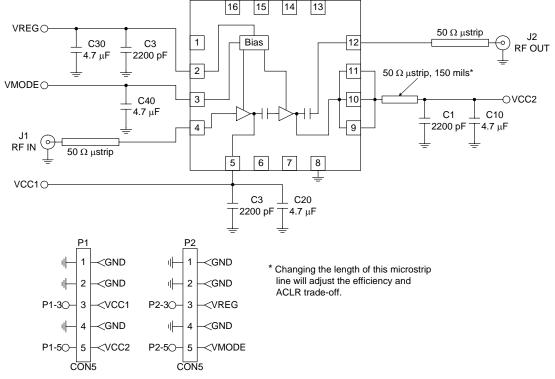








Evaluation Board Schematic - CDMA







Electrostatic Discharge Sensitivity

Human Body Model (HBM)

Figure 3 shows the HBM ESD sensitivity level for each pin to ground. The ESD test is in compliance with JESD22-A114.

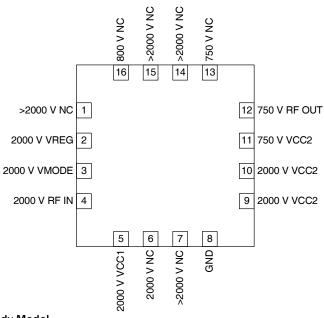


Figure 3. ESD Level - Human Body Model

Machine Model (MM)

Figure 4 shows the MM ESD sensitivity level for each pin to ground. The ESD test is in compliance with JESD22-A115.

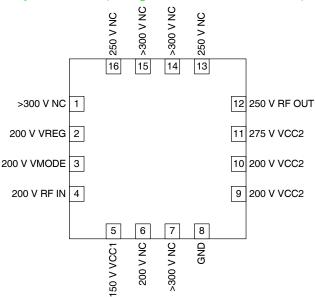


Figure 4. ESD Level - Machine Model



PCB Design Requirements

PCB Surface Finish

The PCB surface finish used for RFMD's qualification process is electroless nickel, immersion gold. Typical thickness is 3µinch to 8µinch gold over 180µinch nickel.

PCB Land Pattern Recommendation

PCB land patterns for PFMD components are based on IPC-7351 standards and RFMD empirical data. The pad pattern shown has been developed and tested for optimized assembly at RFMD. The PCB land pattern has been developed to accommodate lead and package tolerances. Since surface mount processes vary from company to company, careful process development is recommended.

PCB Metal Land Pattern

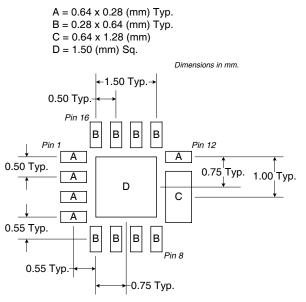


Figure 1. PCB Metal Land Pattern (Top View)





PCB Solder Mask Pattern

Liquid Photo-Imageable (LPI) solder mask is recommended. The solder mask footprint will match what is shown for the PCB metal land pattern with a 2mil to 3mil expansion to accommodate solder mask registration clearance around all pads. The center-grounding pad shall also have a solder mask clearance. Expansion of the pads to create solder mask clearance can be provided in the master data or requested from the PCB fabrication supplier.

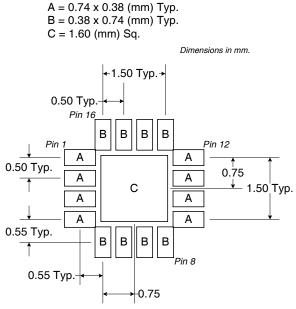


Figure 2. PCB Solder Mask Pattern (Top View)

Thermal Pad and Via Design

The PCB land pattern has been designed with a thermal pad that matches the die paddle size on the bottom of the device.

Thermal vias are required in the PCB layout to effectively conduct heat away from the package. The via pattern has been designed to address thermal, power dissipation and electrical requirements of the device as well as accommodating routing strategies.

The via pattern used for the RFMD qualification is based on thru-hole vias with 0.203mm to 0.330mm finished hole size on a 0.5mm to 1.2mm grid pattern with 0.025mm plating on via walls. If micro vias are used in a design, it is suggested that the quantity of vias be increased by a 4:1 ratio to achieve similar results.





Tape and Reel Information

Carrier tape basic dimensions are based on EIA481. The pocket is designed to hold the part for shipping and loading onto SMT manufacturing equipment, while protecting the body and the solder terminals from damaging stresses. The individual pocket design can vary from vendor to vendor, but width and pitch will be consistent.

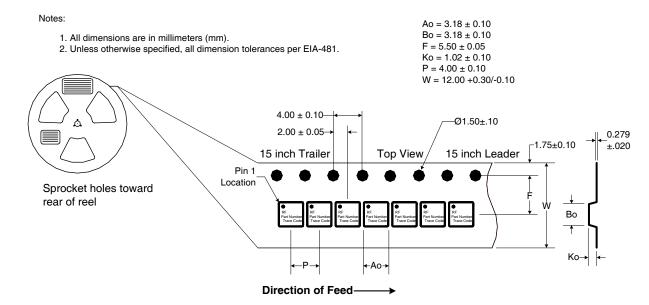
Carrier tape is wound or placed onto a shipping reel either 330 mm (13 inches) in diameter or 178 mm (7 inches) in diameter. The center hub design is large enough to ensure the radius formed by the carrier tape around it does not put unnecessary stress on the parts.

Prior to shipping, moisture sensitive parts (MSL level 2a-5a) are baked and placed into the pockets of the carrier tape. A cover tape is sealed over the top of the entire length of the carrier tape. The reel is sealed in a moisture barrier, ESD bag, which is placed in a cardboard shipping box. It is important to note that unused moisture sensitive parts need to be resealed in the moisture barrier bag. If the reels exceed the exposure limit and need to be rebaked, most carrier tape and shipping reels are not rated as bakeable at 125 °C. If baking is required, devices may be baked according to section 4, table 4-1, column 8 of Joint Industry Standard IPC/JEDEC J-STD-033A.

The following table provides useful information for carrier tape and reels used for shipping the devices described in this document.

RFMD Part Number	Reel Diameter Inch (mm)	Hub Diameter Inch (mm)	Width (mm)	Pocket Pitch (mm)	Feed	Units per Reel
RF3163TR7	7 (178)	2.4 (61)	12	4	Single	2500

QFN (Carrier Tape Drawing with Part Orientation)



RF3163

